

Amendment to the Substitute Specification

Please amend the paragraph beginning on page 20, line 11 as follows:

Therefore, the semiconductor laser component 1 and the submount 2 are joined after a stress has occurred due to ~~the~~by the pressure bonding, and also after releasing the pressure bond of the collet 4, stresses created by pressure bonding remain in the semiconductor laser component 1.

Please amend the paragraph beginning on page 21, line 4 as follows:

In general, when current flows in the semiconductor laser component 1 by applying a stress of 100MPa or more to the light emitting region, crystals are transposed, which deteriorate the laser characteristic or destroy the semiconductor laser component 1. Conventionally, since the residual stress was small in the semiconductor laser component 1, the destruction of the semiconductor laser component 1 due to the crystal transposition did not occur. However, with the increase of the residual stress accompanied by the recent high power, the semiconductor laser component 1 ~~is~~can be destroyed due to the crystal dislocation.

Please amend the paragraph beginning on page 21, line 13 as follows:

In contrast, in this embodiment, in order to decrease the residual stress of the semiconductor laser component 1, as shown in Fig. 1, before holding the semiconductor laser component 1 by the collet 4, the collet 4 is heated by the exothermic coil 6 to a temperature that is more than a fusing point of the bonding member 3 and heating of the heating table 5 and the collet 4 ~~is~~are simultaneously terminated at the time of cooling.